

## **isc Silicon PNP Darlington Power Transistor**

#### **DESCRIPTION**

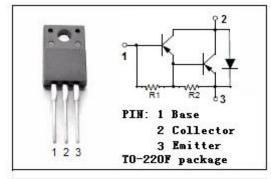
- High DC Current Gain: h<sub>FE</sub>= 2000(Min)@ (V<sub>CE</sub>= -2V, I<sub>C</sub>= -5A)
- · Large Current Capability and Wide ASO.
- · Low collector-to-emitter saturation voltage
- Complement to Type 2SD1827
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

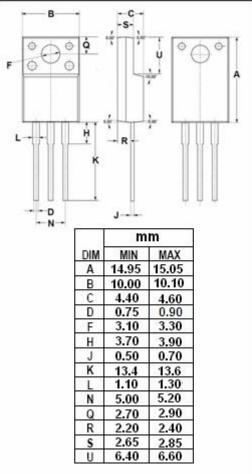


• Designed for use in control of motor drivers, printer hammer drivers, and constant-voltage regulators.

### ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	lector-Base Voltage -70		
V <sub>CEO</sub>	Collector-Emitter Voltage	V		
$V_{EBO}$	Emitter-Base Voltage	nitter-Base Voltage -6		
Ic	Collector Current-Continuous	-10	А	
Ісм	Collector Current-Peak	-15	Α	
Pc	Collector Power Dissipation @T <sub>a</sub> =25℃	2	W	
	Collector Power Dissipation @T <sub>C</sub> =25°C	30		
TJ	Junction Temperature	150	$^{\circ}$	
T <sub>stg</sub>	Storage Temperature	-55~150	$^{\circ}$ C	







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2SB1225

#### **ELECTRICAL CHARACTERISTICS**

Tj=25℃ unless otherwise specified

1j-25 © unless otherwise specified									
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT			
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -50mA; R <sub>BE</sub> = ∞	-60			V			
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I <sub>C</sub> = -5mA; I <sub>E</sub> = 0	-70			V			
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -5A; I <sub>B</sub> = -10mA			-1.5	V			
$V_{\text{BE}(\text{sat})}$	Base-Emitter Saturation Voltage	I <sub>C</sub> = -5A; I <sub>B</sub> = -10mA			-2.0	V			
І <sub>СВО</sub>	Collector Cutoff Current	V <sub>CB</sub> = -40V; I <sub>E</sub> = 0			-100	μ <b>А</b>			
І <sub>ЕВО</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> = 0			-3.0	mA			
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = -5A; V <sub>CE</sub> = -2V	2000						
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = -5A; V <sub>CE</sub> = -5V		20		MHz			
Switching Times									
t <sub>on</sub>	Turn-on Time			0.5		μ <b>S</b>			
t <sub>stg</sub>	Storage Time	$I_{C}$ = -5A, $I_{B1}$ = - $I_{B2}$ = -5mA, $V_{CC}$ = -20V; $R_{L}$ = 4 $\Omega$		1.5		μ <b>S</b>			
t <sub>f</sub>	Fall Time			1.7		μ <b>S</b>			

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